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Contents

Foreword 1

Preface 3

1. Plenary Lectures

Depth profiling using ultra-low-energy secondary ion mass spectrometry
M.G. Dowsett 5

Prospects for imaging TOF-SIMS: from fundamentals to biotechnology
N. Winograd 13

2. Sputtering, Cluster and Ion Formation

Apparent and real transient effects in SIMS depth profiling using oxygen bombardment
K. Wittmaack 20

The dose dependence of Si sputtering with low energy ions in shallow depth profiling
D.W. Moon and H.I. Lee 27

On the correlation between Si^+ yields and surface oxygen concentration using in situ SIMS-LEIS
T. Janssens, C. Huyghebaert, W. Vandervorst, A. Gildenpfennig and H.H. Brongersma 30

Oxygen-ion-induced ripple formation on silicon: evidence for phase separation and tentative model
Y. Homma, A. Takano and Y. Higashi 35

Doubly versus singly positively charged oxygen ions back-scattered from a silicon surface under dynamic O_2^+ bombardment
K. Franzreb, P. Williams, J. Lörinčík and Z. Šroubek 39

Surface roughening of silicon under ultra-low-energy cesium bombardment
Y. Kataoka, K. Yamazaki, M. Shigeno, Y. Tada and K. Wittmaack 43

Ionization probability of atoms and molecules sputtered from a cesium covered silver surface
S. Meyer, C. Staudt and A. Wucher 48

Quantitative depth profiling at silicon/silicon oxide interfaces by means of Cs^+ sputtering in negative mode by ToF-SIMS: a full spectrum approach
S. Ferrari, M. Perego and M. Fanciulli 52

Transient sputter yields, build-up of the altered layer and Ge-segregation as a function of the O_2^+ ion-fluence in SiGe
C. Huyghebaert, B. Brijs, T. Janssens and W. Vandervorst 56

Simulation of oxide sputtering and SIMS depth profiling of delta-doped layer
Y. Yamamura and M. Ishida 62

Big molecule ejection—SIMS vs. MALDI
B.J. Garrison, A. Delcorte, L.V. Zhigilei, T.E. Itina, K.D. Krantzman, Y.G. Yingling, C.M. McQuaw, E.J. Smiley and N. Winograd 69

Investigation of the depth range through ultra-thin carbon films on magnetic layers by time-of-flight secondary ion mass spectrometry
N. Tadokoro, M. Yuki and K. Osakabe 72

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K. Wittmaack 20

The dose dependence of Si sputtering with low energy ions in shallow depth profiling
D.W. Moon and H.I. Lee 27

On the correlation between Si^+ yields and surface oxygen concentration using in situ SIMS-LEIS
T. Janssens, C. Huyghebaert, W. Vandervorst, A. Gildenpfennig and H.H. Brongersma 30

Oxygen-ion-induced ripple formation on silicon: evidence for phase separation and tentative model
Y. Homma, A. Takano and Y. Higashi 35

Doubly versus singly positively charged oxygen ions back-scattered from a silicon surface under dynamic O_2^+ bombardment
K. Franzreb, P. Williams, J. Lörinčík and Z. Šroubek 39

Surface roughening of silicon under ultra-low-energy cesium bombardment
Y. Kataoka, K. Yamazaki, M. Shigeno, Y. Tada and K. Wittmaack 43

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S. Meyer, C. Staudt and A. Wucher 48

Quantitative depth profiling at silicon/silicon oxide interfaces by means of Cs^+ sputtering in negative mode by ToF-SIMS: a full spectrum approach
S. Ferrari, M. Perego and M. Fanciulli 52

Transient sputter yields, build-up of the altered layer and Ge-segregation as a function of the O_2^+ ion-fluence in SiGe
C. Huyghebaert, B. Brijs, T. Janssens and W. Vandervorst 56

Simulation of oxide sputtering and SIMS depth profiling of delta-doped layer
Y. Yamamura and M. Ishida 62

Big molecule ejection—SIMS vs. MALDI
B.J. Garrison, A. Delcorte, L.V. Zhigilei, T.E. Itina, K.D. Krantzman, Y.G. Yingling, C.M. McQuaw, E.J. Smiley and N. Winograd 69

Investigation of the depth range through ultra-thin carbon films on magnetic layers by time-of-flight secondary ion mass spectrometry
N. Tadokoro, M. Yuki and K. Osakabe 72

Ionization probability of sputtered cluster anions: C_n^- and Si_n^-
H. Gnaser 78

Dynamic behavior of sputtering of implanted projectiles and target atoms under high fluence gallium ion bombardment
K. Ohya 82

Electron transfer in ion interactions with chlorine covered silver surfaces
E.M. Staicu-Casagrande, L. Guillemot, S. Lacombe and V.A. Esaulov 86

Towards a model for the formation of positive Si^+ ions
T. Janssens, C. Huyghebaert and W. Vandervorst 90

Work function change caused by alkali ion sputtering
A. Villegas, Yu. Kudriavtsev, A. Godines and R. Asomoza 94

Mass-resolved low-energy back-scattering of alkali ions
K. Franzreb and P. Williams 98

Mechanism of metal cationization in organic SIMS
I. Wojciechowski, A. Delcorte, X. Gonze and P. Bertrand 102

The formation of singly and doubly cationized oligomers in SIMS
A. Delcorte, I. Wojciechowski, X. Gonze, B.J. Garrison and P. Bertrand 106

Nanocrystals depth profiling by means of Cs^+ in negative polarity with dual beam ToF-SIMS
M. Perego, S. Ferrari, S. Spiga and M. Fanciulli 110

Investigation of the cluster ion formation process for inorganic compounds in static SIMS
F. Aubriet, C. Poleunis and P. Bertrand 114

The unimolecular decay of $Al_n^{\pm}$ and $Si_n^{\pm}$ sputtered clusters
N.Kh. Dzhemilev, A.D. Bekkerman, S.E. Maksimov and V.I. Tugushev 118

Features of non-additive sputtering for various "molecular projectile–solid" systems
S.F. Belykh, A.P. Kovarsky, V.V. Palitsin, A. Adriaens and F. Adams 122

Effect of the projectile parameters on the charge state formation process in solid sputtering
S.F. Belykh, V.V. Palitsin, A. Adriaens and F. Adams 126

The energy spectra of secondary ions sputtered from Si and SiGe by ultra-low-energy primary ions
J. Bellingham and M.G. Dowsett 130

Ionization probability changes of the Si^+ ions during the transient for 3 keV O_2^- bombardment of Si
C. Huyghebaert, T. Janssens, B. Brijs and W. Vandervorst 134

Simulation of SiO_2 build-up in silicon under oxygen bombardment
B. Guzmán, J.J. Serrano, J.M. Blanco, M. Aguilar and O. Ameziane 139

MD simulation of cluster ejection due to sputtering by polyatomic projectiles
T. Muramoto and Y. Yamamura 143

Enhancement of cluster yield under gold dimer oblique bombardment of the silicon surface
M. Medvedeva, I. Wojciechowski and B.J. Garrison 148

Observation of ripple formation on O_2^--irradiated GaN surfaces using atomic force microscopy
M. Kanazawa, A. Takano, Y. Higashi, M. Suzuki and Y. Homma 152

Transient effects induced through ripple topography growth during Cs^+ depth profile analysis of Si at high incidence angles
P.A.W. van der Heide, M.S. Lim, S.S. Perry and J. Bennett 156

3. Molucular Fragment Emission

Molecular SIMS for organic layers: new insights
P. Bertrand, A. Delcorte and B.J. Garrison 160

A microscopic view of organic sample sputtering
A. Delcorte, P. Bertrand and B.J. Garrison 166

Ion-to-neutral conversion in time-of-flight secondary ion mass spectrometry
W. Szymczak and K. Wittmaack 170

ToF-SIMS characterization of molecular ions from Fomblin Z-DOL on Ag substrates
Y. Abe and H. Okuhira 175

Effects of sample preparation on ion yield in the study of inorganic salts by s-SIMS
F. Aubriet, C. Poleunis and P. Bertrand 180

Determination of nitrogen in silicon carbide by secondary ion mass spectrometry
B. Ya Ber, D.Yu. Kazantsev, A.P. Kovarsky and R.R. Yafaev 184

4. Focused Ion Beams/Microanalysis

Cation Mass Spectrometer: towards an optimisation of MCs_x^+ cluster analysis
T. Wirtz, H.-N. Migeon and H. Scherrer 189

Nanoscale SIMS analysis: the next generation in local analysis
M. Nojima, B. Tomiyasu, Y. Kanda, M. Owari and Y. Nihei 194

Prospects for imaging with TOF-SIMS using gold liquid metal ion sources
A.V. Walker and N. Winograd 198

Rapid screening of molecular arrays using imaging TOF-SIMS
J.Y. Xu, R.M. Braun and N. Winograd 201

Development of a chemically assisted micro-beam etching system for three-dimensional microanalysis
Y. Tanaka, M. Karashima, K. Takanashi, T. Sakamoto, M. Owari and Y. Nihei 205

5. Cluster/Molecular Ion Beams

Secondary ion mass spectrometry using cluster primary ion beams
G. Gillen and A. Fahey 209

Secondary ion mass spectrometry with gas cluster ion beams
N. Toyoda, J. Matsuo, T. Aoki, I. Yamada and D.B. Fenner 214

Development of a C_{60}^+ ion gun for static SIMS and chemical imaging
S.C.C. Wong, R. Hill, P. Blenkinsopp, N.P. Lockyer, D.E. Weibel and J.C. Vickerman 219

Development and experimental application of a gold liquid metal ion source
N. Davies, D.E. Weibel, P. Blenkinsopp, N. Lockyer, R. Hill and J.C. Vickerman 223

6. Post-Ionization, SNMS

A resonance photoionization sputtered neutral mass spectrometry instrument for submicron microarea analysis of ULSI devices
H. Shichi, S. Osabe, M. Sugaya, T. Ino, H. Kakibayashi, K. Kanehori and Y. Mitsui 228

Trace element analysis of precious metals in minerals by time-of-flight resonance ionization mass spectrometry
S.S. Dimov and S.L. Chryssoulis 235

Nonresonant Laser–SNMS and TOF–SIMS analysis of sub-μm structures
F. Kollmer, N. Bourdos, R. Kamischke and A. Benninghoven 238

Estimation of useful yield in surface analysis using single photon ionisation
B.V. King, M.J. Pellin, J.F. Moore, I.V. Veryovkin, M.R. Savina and C.E. Tripa 244

Energy distributions and excitation probability of nickel atoms sputtered from Ni_3Al, NiAl and Ni
M. Tan and B.V. King 248

7. Shallow Depth Profiling

Steady-state surface concentration profiles of primary ion species during secondary ion mass spectrometry measurements
S. Yoshikawa, H. Morita, F. Toujou, T. Matsunaga and K. Tsukamoto 252

Surface roughening effect in sub-keV SIMS depth profiling
R. Liu, C.M. Ng and A.T.S. Wee 256

Correction for the loss of depth resolution with accurate depth calibration when profiling with Cs^+ at angles of incidence above 50° to normal
J.H. Kelly, M.G. Dowsett, P. Augustus and R. Beanland 260

Accurate SIMS depth profiling for ultra-shallow implants using backside SIMS
C. Hongo, M. Tomita, M. Takenaka and A. Murakoshi 264

Detailed evaluation of the analytical resolution function
K. Wittmaack 268

On determining accurate positions, separations, and internal profiles for delta layers
M.G. Dowsett, J.H. Kelly, G. Rowlands, T.J. Ormsby, B. Guzmán, P. Augustus and R. Beanland 273

Low energy dual beam depth profiling: influence of sputter and analysis beam parameters on profile performance using TOF-SIMS
T. Grehl, R. Möllers and E. Niehuis 277

D-SIMS and ToF-SIMS quantitative depth profiles comparison on ultra thin oxynitrides
M. Bersani, D. Giubertoni, M. Barozzi, E. Elacob, L. Vanzetti, M. Anderle, P. Lazzeri, B. Crivelli and F. Zanderigo 281

Transient processes and structural transformations in Si_xGe_{1-x} layers during oxygen implantation and sputtering
D. Krüger, A.A. Efremov, J. Murota, B. Tillack, R. Kurps and G.Ph. Romanova 285

Metal implant standards for surface analysis by TOF-SIMS and dynamic SIMS: comparison with TRIM simulation
A.V. Li-Fatou and M. Douglas 290

Evaluation of SIMS depth resolution using delta-doped multilayers and mixing–roughness-information depth model
A. Takano, Y. Homma, Y. Higashi, H. Takenaka, S. Hayashi, K. Goto, M. Inoue and R. Shimizu 294

SIMS study of depth profiles of delta-doped boron/silicon alternating layers by low-energy ion beams
S. Hayashi, A. Takano, H. Takenaka and Y. Homma 298

Multiple As delta layered Si thin films for SIMS quantification and depth scale calibration
S.B. Cho, H.K. Shon, H.J. Kang, T.E. Hong, H.K. Kim, H.I. Lee, K.J. Kim and D.W. Moon 302

Transient effects noted during Cs^+ depth profile analysis of Si at high incidence angles
P.A.W. van der Heide and J. Bennett 306

Using SIMS and the NIST standard reference material #2137 to calibrate standards used in the $^{11}B(p, \alpha)^8Be$ nuclear reaction analysis of B in Si
C.W. Magee and D.C. Jacobson 310

The features of using of BO_2^- secondary ions for SIMS depth profiling of shallow boron implantation in silicon
S.G. Simakin and V.K. Smirnov 314

Six months repeatability of D-SIMS depth profile using an ultra-low-energy probe
Z. Li, T. Hoshi and R. Oiwa 318

Characteristics of ultra-low-energy Cs^+ ion beam bombardments
Z. Li, T. Hoshi and R. Oiwa 323

Surprisingly large apparent profile shifts of As and Sb markers in Si bombarded with ultra-low-energy Cs ion beams
Y. Kataoka, M. Shigeno, Y. Tada and K. Wittmaack 329

SIMS backside depth profiling of ultra shallow implants
K.L. Yeo, A.T.S. Wee, A. See, R. Liu and C.M. Ng 335

Dual ion beam analysis of boron implanted SiO_2/silicon interface
S. Hayashi and K. Yanagihara 339

A floating low energy electron gun (FLEG) for charge compensation in SIMS and other applications
R. Gibbons, M.G. Dowsett, J. Kelly, P. Blenkinsopp, R. Hill, D. Richards and N. Loibl 343

Comparison between Xe^+ and O_2^+ primary ions, at low impact energy, on B delta-doping, SiGe–Si superlattice and Al/Ti multilayer structures
F. Laugier, P. Holliger, J.C. Dupuy and N. Baboux 348

B_4C/Mo/Si and Ta_2O_5/Ta nanostructures analysed by ultra-low energy argon ion beams
P. Konarski and A. Mierzejewska 354

SIMS depth profiling of N and In in a ZnO single crystal
D.-C. Park, I. Sakaguchi, N. Ohashi, S. Hishita and H. Haneda 359

Determination of the variation in sputter yield in the SIMS transient region using MEIS
M.G. Dowsett, T.J. Ormsby, F.S. Gard, S.H. Al-Harthi, B. Guzmán, C.F. McConville, T.C.Q. Noakes and P. Bailey 363

Investigating oxygen flooding at oblique 2 and 1 keV oxygen sputtering for microelectronics support applications
F. Jahnel and R. von Criegern 367

8. Semiconductors/Microelectronics

An (un)solvable problem in SIMS: B-interfacial profiling
W. Vandervorst, T. Janssens, R. Loo, M. Caymax, I. Peytier, R. Lindsay, J. Frühauf, A. Bergmaier and G. Dollinger 371

Estimation of ultra-shallow implants using SIMS, NRA and chemical analysis
M. Tomita, M. Suzuki, T. Tachibe, S. Kozuka and A. Murakoshi 377

LEXES and SIMS as complementary techniques for full quantitative characterization of nanometer structures
C. Hombourger, P.F. Staub, M. Schuhmacher, F. Desse, E. de Chambost and C. Hitzman 383

Copper drift in low dielectric constant insulator films caused by O_2^+ primary ion beam
K. Shibahara, D. Onimatsu, Y. Ishikawa, T. Oda and T. Kikkawa 387

Depth scale calibration of SIMS depth profiles by means of an online crater depth measurement technique
E. De Chambost, P. Monsallut, B. Rasser and M. Schuhmacher 391

Extremely deep SIMS profiling: oxygen in FZ silicon
A. Barcz, M. Zielinski, E. Nossarzewska and G. Lindstroem 396

TOF-SIMS as a rapid diagnostic tool to monitor the growth mode of thin (high k) films
T. Conard, W. Vandervorst, J. Petry, C. Zhao, W. Besling, H. Nohira and O. Richard 400

Application of SIMS in microelectronics
K. Tsukamoto, S. Yoshikawa, F. Toujou and H. Morita 404

SIMS depth profiling of advanced gate dielectric materials
J. Bennett, C. Gondran, C. Sparks, P.Y. Hung and A. Hou 409

Quantitative depth profiling of SiO_xN_y layers on Si
J.G.M. van Berkum, M.J.P. Hopstaken, J.H.M. Snijders, Y. Tamminga and F.N. Cubaynes 414

SIMS and high-resolution RBS analysis of ultrathin SiO_xN_y films
K. Kimura, K. Nakajima, H. Kobayashi, S. Miwa and K. Satori 418

Quantitative depth profiling of nitrogen in ultrathin oxynitride film with low energy SIMS
H.K. Shon, H.J. Kang, T.E. Hong, H.S. Chang, K.J. Kim, H.K. Kim and D.W. Moon 423

Solubility limits of dopants in 4H–SiC
M.K. Linnarsson, U. Zimmermann, J. Wong-Leung, A. Schöner, M.S. Janson, C. Jagadish and B.G. Svensson 427

Adventures in molecular electronics: how to attach wires to molecules
B.C. Haynie, A.V. Walker, T.B. Tighe, D.L. Allara and N. Winograd 433

Gate oxide properties investigated by TOF-SIMS profiles on CMOS devices
F. Zanderigo, D. Brazzelli, S. Rocca, A. Pregnolato, A. Grossi and G. Queirolo 437

TOF-SIMS depth profiling of SIMON
G. Xin, G. Dong, C. Xu, C. Liangzhen, O. Brox and A. Benninghoven 441

TOF-SIMS study of adhesive residuals on device contact pads after wafer taping and backgrinding
P. Lazzeri, G. Franco, M. Garozzo, C. Gerardi, E. Iacob, A. Lo Faro, A. Privitera, L. Vanzetti and M. Bersani 445

TOF-SIMS measurement of ultra-thin SiO_2 films prepared by the graded-etching method
T. Shibamori, Y. Muraji, N. Man and A. Karen 449

SIMS analysis of insulating multilayer including silicon nitride
Y. Ueki, T. Kawashima and O. Ishiwata 453

SIMS quantification of low concentration of nitrogen doped in silicon crystals
N. Fujiyama, A. Karen, D.B. Sams, R.S. Hockett, K. Shingu and N. Inoue 457

Round robin study of chlorine, sulfur and carbon in copper films from Taiwan SIMS users
C.Y. Chen, Y.C. Ling, J.F. Hwang, J.H. Lee, M.L. Wen, M.C. Hwang, G.C. Lin and R.C. Deng 461

SIMS round-robin study of depth profiling of arsenic implants in silicon
M. Tomita, T. Hasegawa, S. Hashimoto, S. Hayashi, Y. Homma, S. Kakehashi, Y. Kazama, K. Koezuka, H. Kuroki, K. Kusama, Z. Li, S. Miwa, S. Miyaki, Y. Okamoto, K. Okuno, S. Saito, S. Sasaki, H. Shichi, H. Shinohara, F. Toujou, Y. Ueki and Y. Yamamoto 465

Evaluation of the Cu-CMP process by TOF-SIMS and XPS: time dependence of Cu surface adsorbents and oxidation states
A. Nishi, M. Sado, T. Miki and Y. Fukui 470

Surface chemical state analysis of electroplated Cu film under Cu-CMP process by means of TOF–SIMS
H. Miyoshi, R. Saito and M. Kudo 473

SIMS analysis of hydrogen diffusion and trapping in CVD polycrystalline diamond
F. Jomard and D. Ballutaud 478

Secondary ion mass spectrometry analysis of In-doped p-type GaN films
C.Y. Chiou, C.C. Wang, Y.C. Ling and C.I. Chiang 482

SIMS depth profiling of InGaAsN/InAlAs quantum wells on InP
M. Maier, D. Serries, T. Geppert, K. Köhler, H. Güllich and N. Herres 486

The effect of Se and Zn pre-deposition on thermal diffusion of elements across the ZnSe/GaAs interface studied by SIMS
F.S. Gard, J.D. Riley, M.G. Dowsett and K. Prince 490

A correlation of TOF-SIMS and TXRF for the analysis of trace metal contamination on silicon and gallium arsenide
I. Mowat, P. Lindley and L. McCaig 495

Charge compensation using optical conductivity enhancement and simple analytical protocols for SIMS of resistive $Si_{1-x}Ge_x$ alloy layers
M.G. Dowsett, R. Morris, P.-F. Chou, S.F. Corcoran, H. Kheyrandish, G.A. Cooke, J.L. Maul and S.B. Patel 500

SIMS study of oxygen in- and out-diffusion in SIMOX wafers during thermal annealing using ^{18}O implantation
S. Hayashi, T. Sasaki, K. Kawamura, A. Matsumura, K. Yanagihara and K. Tanaka 504

Characterization of ion-induced sodium migration in various kinds of silicon oxide films
R. Saito, M. Nagatomo, N. Makino, S. Hayashi and M. Kudo 508

SIMS depth profile of copper in low-k dielectrics under electron irradiation for charge compensation
K. Yamada, N. Fujiyama, J. Sameshima, R. Kamoto and A. Karen 512

Characterization of high-k gate dielectric films using SIMS
T. Yamamoto, N. Morita, N. Sugiyama, A. Karen and K. Okuno 516

Direct determination of p/n junction depth by the emission of matrix complex ions
O.V. Alexandrov, D.Yu. Kazantsev and A.P. Kovarsky 520

Ion-bombardment artifact in TOF-SIMS analysis of $ZrO_2/SiO_2/Si$ stacks
H. De Witte, T. Conard, W. Vandervorst and R. Gijbels 523

Imaging by time-of-flight secondary ion mass spectrometry of plasma patterned metal and oxide thin films
G. Coullerez, J. Baborowski, C. Viornery, Y. Chevolot, N. Xanthopoulos, N. Ledermann, P. Muralt, N. Setter and H.J. Mathieu 527

9. Organic Materials/Polymers

ToF-SIMS quantitative approaches in copolymers and polymer blends
L.T. Weng and C.-M. Chan 532

Analysis of surface composition of isotopic polymer blend based on time-of-flight secondary ion mass spectroscopy
A. Takahara, D. Kawaguchi, K. Tanaka, M. Tozu, T. Hoshi and T. Kajiyama 538

TOF-SIMS characterization of industrial materials: from silicon wafer to polymer
A. Karen, N. Man, T. Shibamori and K. Takahashi 541

Characterization of polymer solar cells by TOF-SIMS depth profiling
C.W.T. Bulle-Lieuwma, W.J.H. van Gennip, J.K.J. van Duren, P. Jonkheijm, R.A.J. Janssen and J.W. Niemantsverdriet 547

G-SIMS of crystallisable organics
I.S. Gilmore and M.P. Seah 551

Surface evolution of polycarbonate/polyethylene terephthalate blends induced by thermal treatments
A. Licciardello, A. Auditore, F. Samperi and C. Puglisi 556

The influence of primary ion bombardment conditions on the secondary ion emission behavior of polymer additives
R. Kersting, B. Hagenhoff, P. Pijpers and R. Verlaek 561

Quantitative analysis of styrene butadiene copolymers using S-SIMS and LA-FTICRMS
D. Ruch, C. Boes, R. Zimmer, J.F. Muller and H.-N. Migeon 566

Antioxidant segregation and crystallisation at polyester surfaces studied by ToF-SIMS
N. Médard, A. Benninghoven, D. Rading, A. Licciardello, A. Auditore, T.M. Duc, H. Montigaud, F. Vernerey, C. Poleunis and P. Bertrand 571

Time-of-flight-SIMS and XPS characterization of metal doped polymers
Th. Gross, I. Retzko, J. Friedrich and W. Unger 575

TOF-SIMS study of organosilane adsorption on model hydroxyl terminated surfaces
L. Houssiau and P. Bertrand 580

TOF-SIMS study on the adsorption behavior of mixtures of a phosphite and a friction modifier onto ferrous material
A. Murase and T. Ohmori 586

Characterization of lubricants for fluid dynamic bearing by TOF-SIMS
F. Toujou, K. Tsukamoto and K. Matsuoka 590

Tribological characterisation of an organic coating by the use of ToF-SIMS
U. Bexell, P. Carlsson and M. Olsson 596

Investigating the difficulty of eliminating flood gun damage in TOF-SIMS
I.S. Gilmore and M.P. Seah 600

Characterization of methyl methacrylate oligomers using secondary ion mass spectrometry, APCI mass spectrometry and molecular orbital theory
T. Takeuchi, K. Iwai, K. Momoji, I. Miyamoto, K. Saiki and K. Hashimoto 605

10. Material Sciences

Elemental distribution analysis of positive electrode material for a nickel metal hydride battery
K. Takanashi, M. Yoshida, T. Sakamoto, N. Ono, Y. Tanaka, M. Owari and Y. Nihei 609

Imaging TOF-SIMS for the surface analysis of silver halide microcrystals
J. Lenaerts, R. Gijbels, L. Van Vaeck, G. Verlinden and I. Geuens 614

Insights into ToF-SIMS analysis of dendritic macromolecules: cationization and PCA to probe their molecular weight on surfaces
G. Coullerez, S. Lundmark, M. Malkoch, H. Magnusson, E. Malmström, A. Hult and H.J. Mathieu 620

A study of defect structures in oxide materials by secondary ion mass spectrometry
H. Haneda 625

Use of isotopic tracers and SIMS analysis for evaluating the oxidation behaviour of protective coatings on nickel based superalloys
A.A. Alibhai, R.J. Chater, D.S. McPhail and B.A. Shollock 630

Determination of proton and oxygen movements in solid oxides by the tracer gases exchange technique and secondary ion mass spectrometry
T. Horita, K. Yamaji, N. Sakai, Y. Xiong, T. Kato, H. Yokokawa and T. Kawada 634

Measurement of oxygen grain boundary diffusion in mullite ceramics by SIMS depth profiling
P. Fielitz, G. Borchardt, M. Schmücker, H. Schneider and P. Willich 639

Speciation of surface gold in pressure oxidized carbonaceous gold ores by TOF-SIMS and TOF-LIMS
S.S. Dimov, S.L. Chryssoulis and R.N. Sodhi 644

ToF-SIMS imaging of dopant diffusion in optical fibers
M. Hellsing, M. Fokine, A. Claesson, L.-E. Nilsson and W. Margulis 648

Light element distribution in ZnO thin film deposited by electron cyclotron resonance assisted chemical vapor deposition
I. Sakaguchi 652

SIMS analysis of multi-diffusion profiles of lanthanides in stabilized zirconias
S. Weber, S. Scherrer, H. Scherrer, M. Kilo, M.A. Taylor and G. Borchardt 656

Low energy SIMS characterisation of ultra thin oxides on ferrous alloys
E.E. Rees, D.S. McPhail, M.P. Ryan, J. Kelly and M.G. Dowsett 660

Hydrogen absorption of $LaNi_5$ after LiOD treatment and surface characterization by TOF-SIMS
C. Izawa, H.-H. Uchida, H. Okuhira and Y. Nishi 665

Chemical characterization of combustion deposits by TOF-SIMS
P. Sjövall, J. Lausmaa, C. Tullin and J. Högberg 669

A new shielded SIMS instrument for analysis of highly radioactive materials
B. Rasser, L. Desgranges and B. Pasquet 673

11. Life Sciences

SIMS ion microscopy as a novel, practical tool for subcellular chemical imaging in cancer research
S. Chandra 679

Fine structures and ion images on fresh frozen dried ultrathin sections by transmission electron and scanning ion microscopy
K. Takaya, M. Okabe, M. Sawataishi, H. Takashima and T. Yoshida 684

Genome diagnostics with TOF-SIMS
H.F. Arlinghaus, M. Ostrop, O. Friedrichs and J.C. Feldner 689

ToF–SIMS chemical mapping study of protein adsorption onto stainless steel surfaces immersed in saline aqueous solutions
C. Poleunis, C. Rubio, C. Compère and P. Bertrand 693

Characterization of adsorbed protein films using time-of-flight-secondary ion mass spectrometry and multivariate analysis
M.S. Wagner and D.G. Castner 698

Quantitative time-of-flight secondary ion mass spectrometry for the characterization of multicomponent adsorbed protein films
M.S. Wagner, M. Shen, T.A. Horbett and D.G. Castner 704

Detection of chlorinated pesticides on the surface of fungus using ToF-SIMS
B. Cliff, D.E. Weibel, N.P. Lockyer, H. Jungnickel, G. Stephens and J.C. Vickerman 710

Zinc detection in the islet of Langerhans by SIMS
M. Okabe, T. Yoshida, R. Yoshii, M. Sawataisi and K. Takaya 714

Detection and quantification of benzodiazepines in hair by ToF-SIMS: preliminary results
J.-N. Audinot, M. Yegles, A. Labarthe, D. Ruch, R. Wennig and H.-N. Migeon 718

TOF-SIMS investigation of the immobilization process of peptide nucleic acids
J.C. Feldner, M. Ostrop, O. Friedrichs, S. Sohn, D. Lipinsky, U. Gunst and H.F. Arlinghaus 722

Subcellular imaging of freeze-fractured cell cultures by TOF-SIMS and Laser-SNMS
M. Fartmann, S. Dambach, C. Kriegeskotte, D. Lipinsky, H.P. Wiesmann, A. Wittig, W. Sauerwein and H.F. Arlinghaus 726

Development of instrumentation for routine ToF-SIMS imaging analysis of biological material
B. Cliff, N.P. Lockyer, C. Corlett and J.C. Vickerman 730

Time-of-flight secondary ion mass spectrometry of fatty acids in rat retina
H. Gong, T. Amemiya, K. Takaya, M. Tozu and Y. Ohashi 734

Changes of vitamins A and E in the rat retina under light and dark conditions detected with TOF-SIMS
T. Amemiya, H. Gong, K. Takaya, M. Tozu and Y. Ohashi 738

Trace elements in lenses of normal Wistar Kyoto rats
A. Kinoshita, H. Gong, T. Amemiya, K. Takaya, M. Tozu and Y. Ohashi 742

12. Environmental Sciences

Application of SIMS to the analysis of environmental samples
H. Seyama 745

Surface composition of atmospheric aerosol: individual particle characterization by TOF-SIMS
R.E. Peterson and B.J. Tyler 751

SIMS depth profiling of working environment nanoparticles
P. Konarski, I. Iwanejko and A. Mierzejewska 757

Analysis of surface composition and internal structure of fly ash particles using an ion and electron multibeam microanalyzer
T. Sakamoto, K. Shibata, K. Takanashi, M. Owari and Y. Nihei 762

ToF-SIMS and XPS characterisation of urban aerosols for pollution studies
P. Lazzeri, G. Clauser, E. Iacob, A. Lui, G. Tonidandel and M. Anderle 767

Analysis of condensation dusts from the heavy oil combustion using TOF-SIMS
S. Oishi, M. Shirahase, M. Sado and R. Oiwa 772

TOF-SIMS measurements for toxic air pollutants adsorbed on the surface of airborne particles
B. Tomiyasu, T. Hoshi, M. Owari and Y. Nihei 775

SIMS depth profiling analysis of electrical arc residues in fire investigation
C.Y. Chen, Y.C. Ling, J.T. Wang and H.Y. Chen 779

TOF-SIMS characterization of planktonic foraminifera
G. Vering, C. Crone, J. Bijma and H.F. Arlinghaus 785

Application of SIMS to silver tarnish at the British Museum
K. Hallett, D. Thickett, D.S. McPhail and R.J. Chater 789

13. Isotopic Ratio and Earth Sciences

High precision isotope micro-imaging of materials
H. Yurimoto, K. Nagashima and T. Kunihiro 793

Oxygen isotopic measurements on the Cameca Nanosims 50
G. Slodzian, F. Hillion, F.J. Stadermann and F. Horreard 798

Silicon isotope fractionation during FZ growth of silicon crystals
Y. Morishita and H. Satoh 802

Application of high precision SIMS ^{26}Al–^{26}Mg analyses to the early solar system chronology
N.T. Kita, S. Mostefaoui, Y.Z. Liu, S. Togashi and Y. Morishita 806

In situ U–Pb dating and REE analyses of phosphates in extraterrestrial materials
K. Terada and Y. Sano 810

Melt contribution to partitioning of trace element between plagioclase and basaltic magma of Fuji volcano, Japan
S. Togashi, N.T. Kita, A. Tomiya, Y. Morishita and N. Imai 814

14. Imaging

High resolution static SIMS imaging by time of flight SIMS
T. Hoshi and M. Kudo 818

Interpretation of TOF-SIMS images: multivariate and univariate approaches to image de-noising, image segmentation and compound identification
B. Tyler 825

Ion image enhancement using in-situ implantation of Cs^+ and O_2^- ions
S. Seki, H. Tamura and W. Saitoh 832

Failure analysis of liquid crystal display panel by time-of-flight secondary ion mass spectrometry
S. Miyaki, A. Yoshida, Y. Yamamoto and K. Takeuchi 836

15. Surface Characterization

Probing molecules on a surface by Cs^+ reactive ion scattering: identification of C_xH_y ($x \leq 4$) hydrocarbons
H. Kang, C.W. Lee, C.H. Hwang and C.M. Kim 842

Surface metal standards produced by ion implantation through a removable layer
B.W. Schueler, C.N. Granger, L. McCaig, J.M. McKinley, J. Metz, I. Mowat, D.F. Reich, S. Smith, F.A. Stevie and M.H. Yang 847

Quantitative analysis of the top 5 nm of boron ultra-shallow implants
J. Bellingham, M.G. Dowsett, E. Collart and D. Kirkwood 851

Time-of-flight secondary ion mass spectrometry (TOF-SIMS) for high-throughput characterization of biosurfaces
S. Roberson, A. Sehgal, A. Fahey and A. Karim 855

Estimation of ToF-SIMS information depth in micro-corrosion analysis
Y. Abe, M. Komatsu and H. Okuhira 859

Chemical state analysis of ZnO/Ag film interface utilizing the matrix effect
Y. Yamamoto, Y. Hayashi, Y. Tachibana, N. Shimodaira and M. Kudo 863

Oxidizing mechanism of beryllium–copper in alkaline solution
H. Kuroki and H. Kawarai 867

Spectral characterization of perfluoropolyethers lubricant irradiated by laser light
L. Zhu and T. Liew 871

Structural characterization of various ionomers by time-of-flight secondary ion mass spectrometry
Y. Lee, S. Han, M.-H. Kwon, H. Lim, Y.-S. Kim, H. Chun and J.-S. Kim 875

List of Chairpersons I

List of Reviewers II

Author Index III

Subject Index XVI